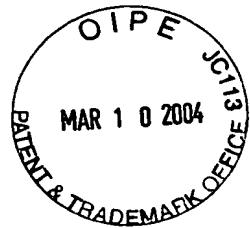


SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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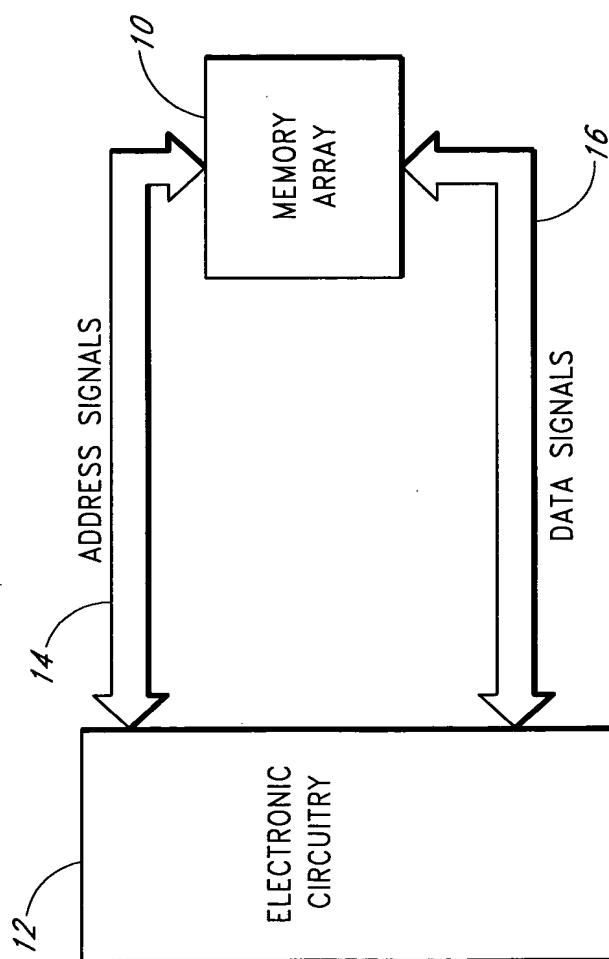


FIG. 1

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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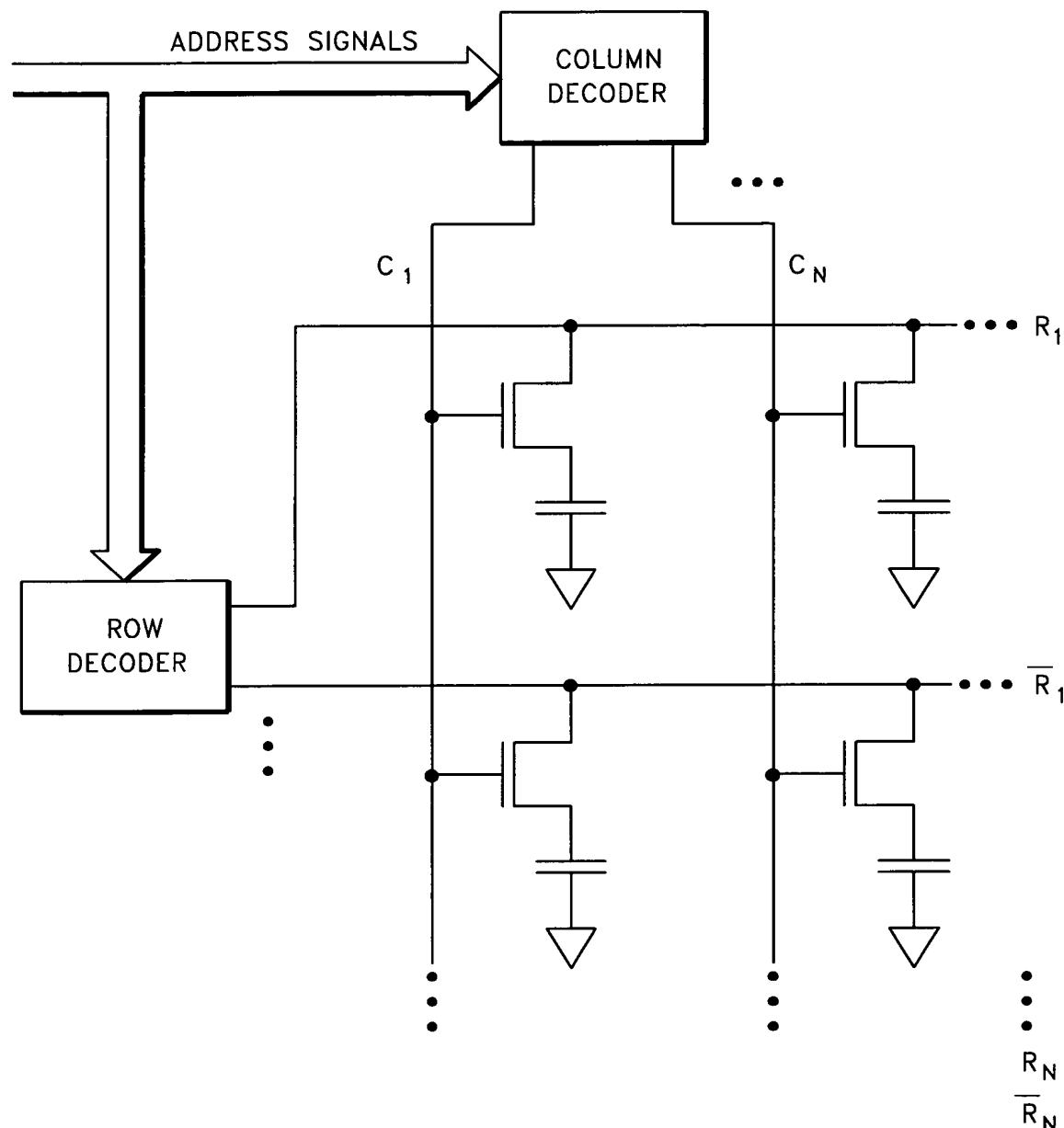


FIG. 2

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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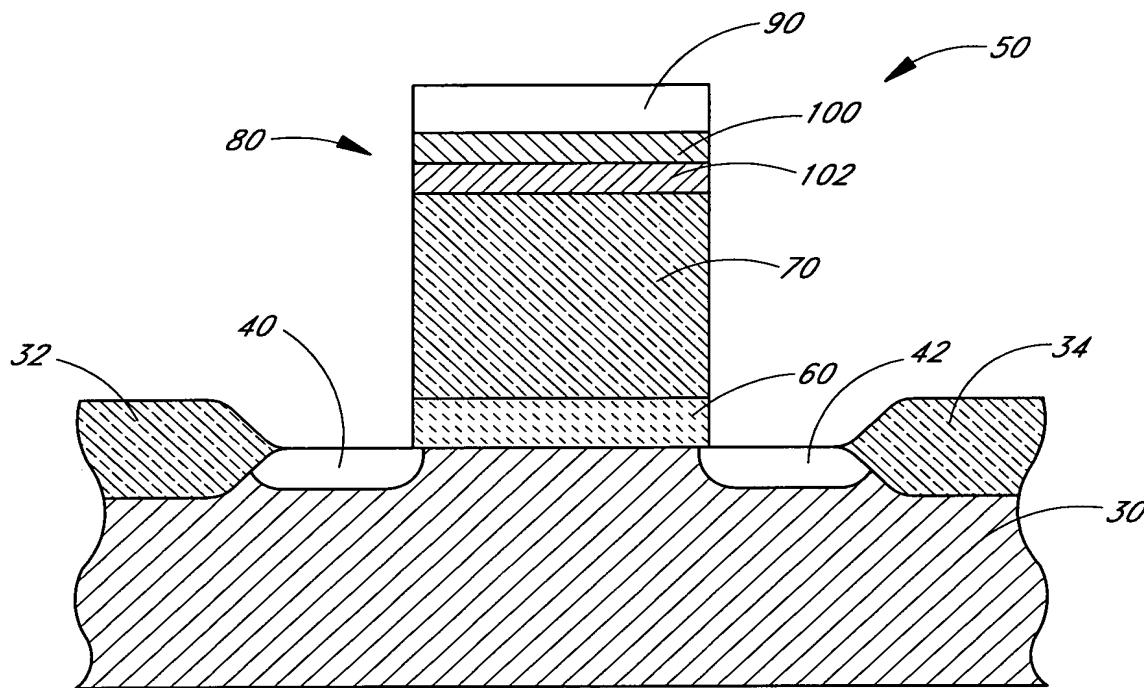


FIG. 3

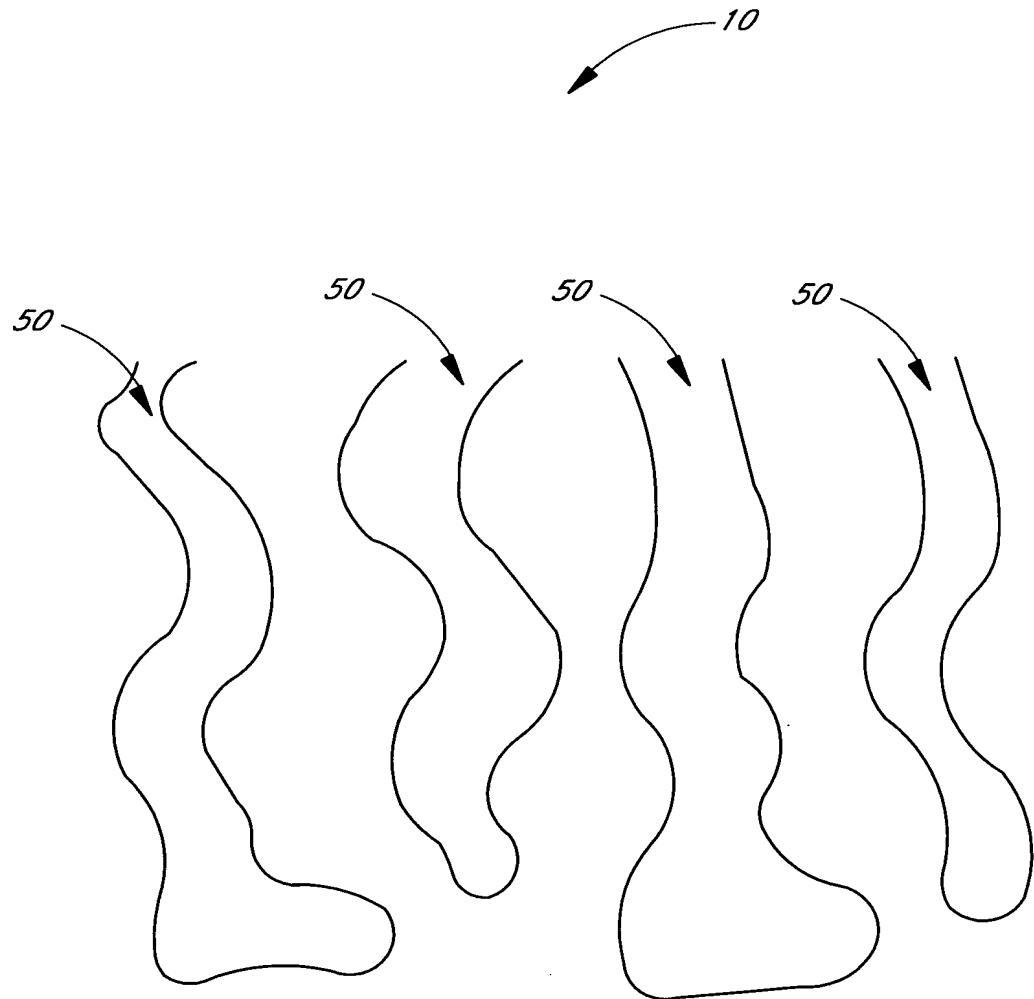


FIG. 4

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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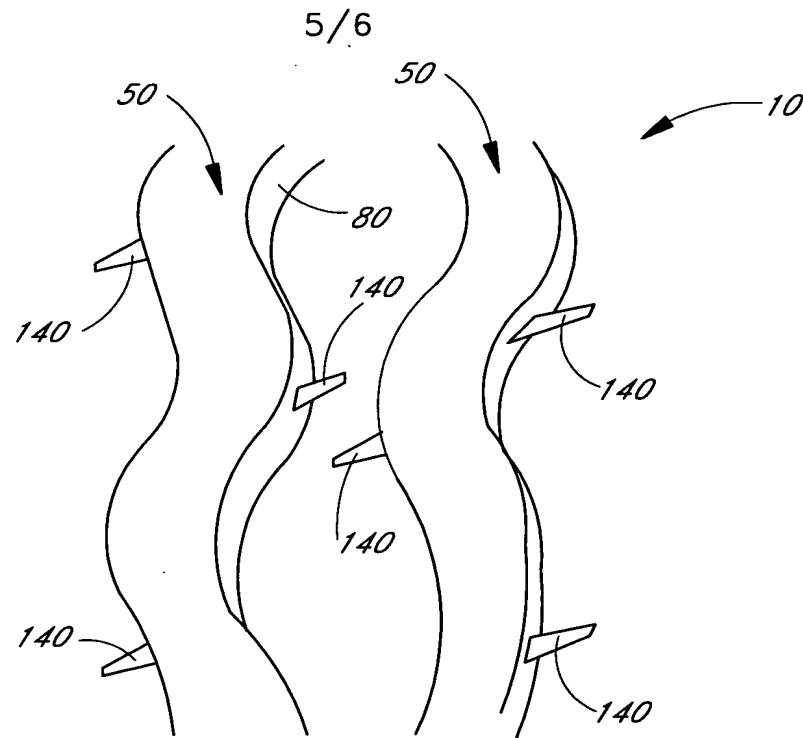


FIG. 5

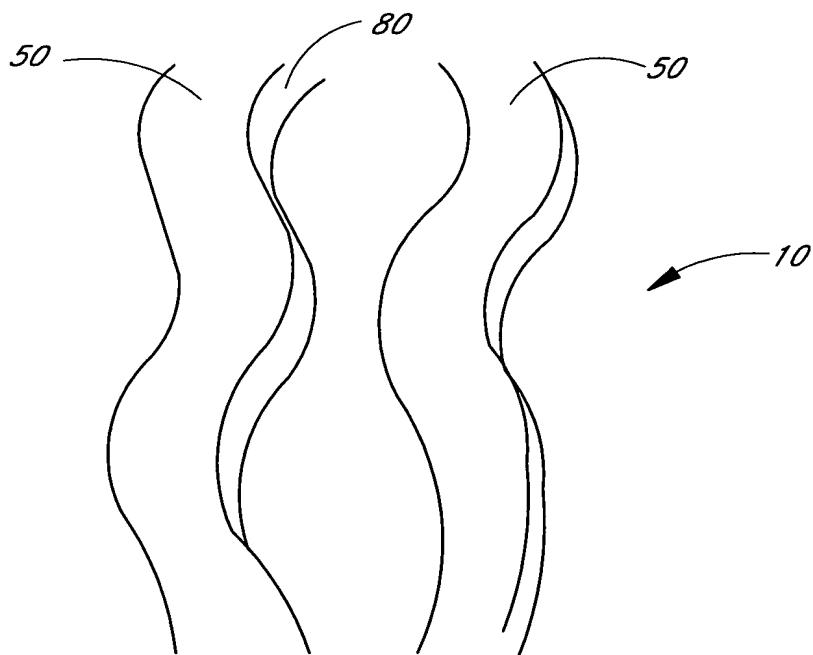


FIG. 6

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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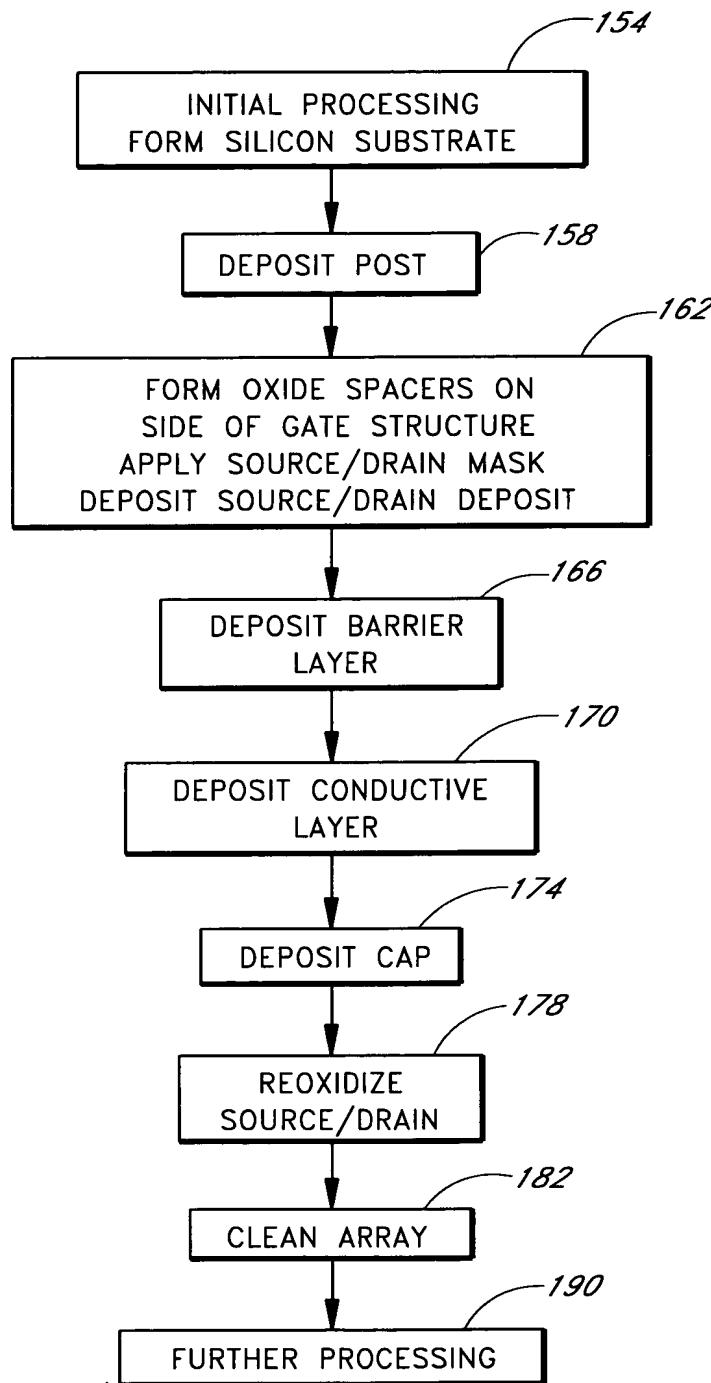


FIG. 7